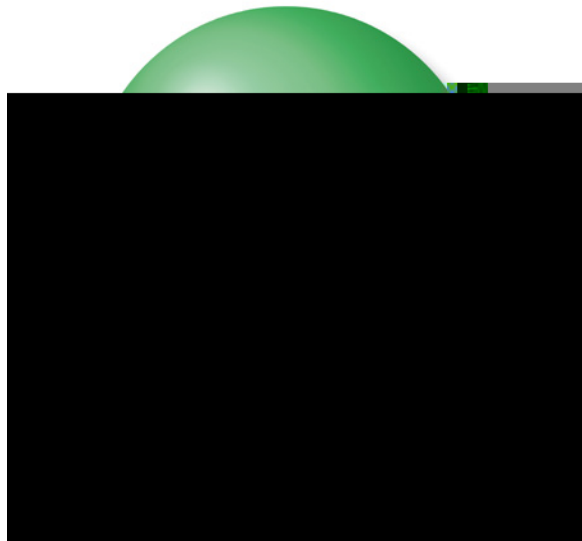




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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

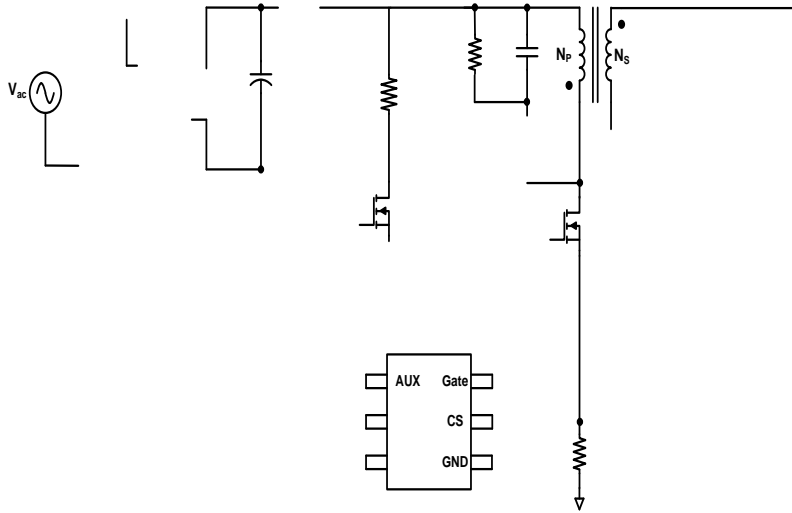


Figure 1. FAN105B Typical Application Schematic

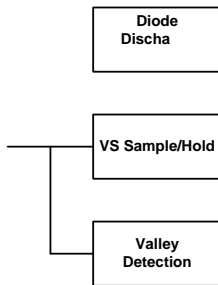


Figure 2. FAN105B Function Block Diagram

PIN FUNCTION DESCRIPTION

Pin #

ABSOLUTE MAXIMUM RATINGS (Note 1,2,3,4)

Parameter

ELECTRICAL CHARACTERISTICS

$V_{DD}=12\text{ V}$ and $T_A=-40\sim 85\text{ C}$ unless noted

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
-----------	-----------------	--------	-----	-----	-----	------

VDD Section

Turn-On Threshold Voltage		V_{DD-ON}	16.5	17.5	18.5	V
Turn-Off Threshold Voltage		V_{DD-OFF}	6.1	6.5	6.9	V
V_{DD} Over-Voltage-Protection Level		V_{DD-OVP}	26.5	28.0	29.5	V
V_{DD} Over-Voltage-Protection De-bounce Time		t_{D-VDD}				

Continues on next page...

ELECTRICAL CHARACTERISTICS

$V_{DD}=12\text{ V}$ and $T_A=-40\sim 85\text{ C}$ unless noted

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Voltage Sampling Section						
Reference Voltage of Constant Voltage Feedback		V_{VR}	2.475	2.500	2.525	V
VS Sampling Phase-Shift Resistance ⁽⁷⁾		$R_{VS-S/H}$		300		k
VS Sampling Phase-Shift Capacitance ⁽⁷⁾		$C_{VS-S/H}$		5		pF
VS Sampling Blanking Time of High Level	I_o over 100mA	t_{VS_BNK-H}	1.65	1.80	2.00	μs
VS Sampling Blanking Time at CC Controlling		t_{VS_BNK-CC}	2.05	2.20	2.35	μs
VS Discharging Time Judgment Threshold Voltage ⁽⁷⁾		$V_{VS-Offset}$	150		250	mV
Voltage Sense Section						
Temperature-Independent Bias Current		I_{TC}	9.0	10.0	11.0	μA

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Typical Performance Characteristics

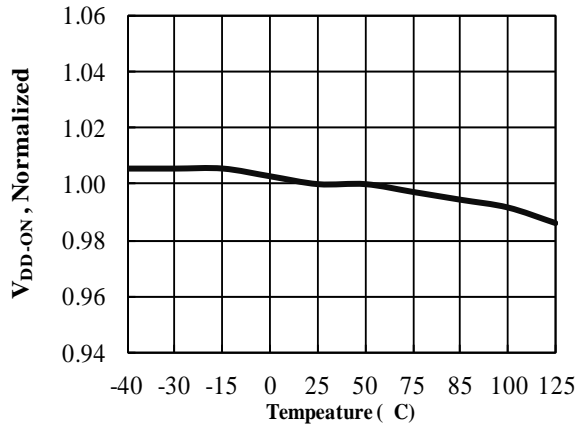


Figure 3. Turn-On Threshold Voltage (V_{DD-ON}) vs. Temperature

Figure 4. Turn-Off Threshold Voltage (V_{DD-OFF}) vs. Temperature

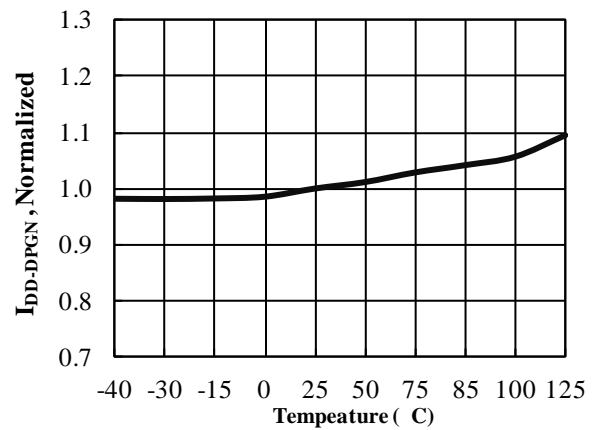


Figure 5. Operating Supply Current (I_{DD-OP}) vs. Temperature

Figure 6. Deep Green Mode Operation Current ($I_{DD-DPGN}$) vs. Temperature

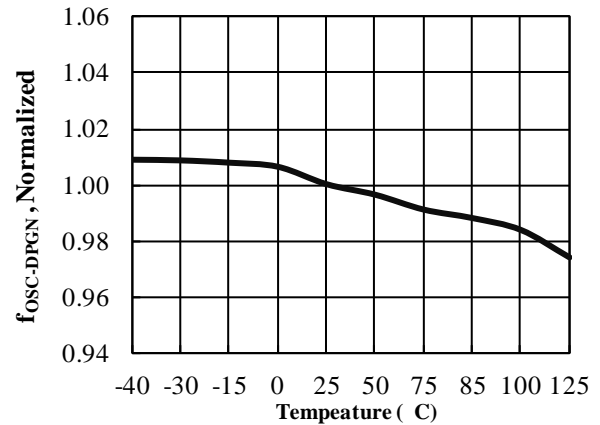
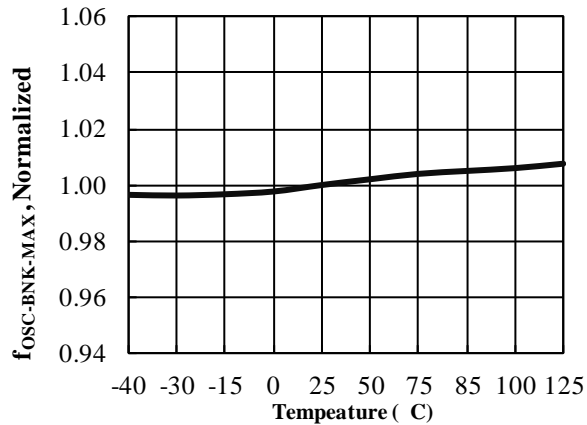


Figure 7. Maximum Operation Frequency of QR Blanking Time ($f_{OSC-BNK-MAX}$) vs. Temperature

Figure 8. Deep Green Mode Operation Frequency ($f_{OSC-DPGN}$) vs. Temperature

Typical Performance Characteristics

Figure 15. Maximum Gate Turn On Time (t_{ON-MAX}) vs. Temperature

Figure 16. Dynamic trigger current threshold (I_{ZTC}) vs. Temperature

Figure 17. Cable Compensation Level 4 Reference Voltage ($V_{VS-CDC4}$) vs. Temperature

Figure 18.

Typical Performance Characteristics

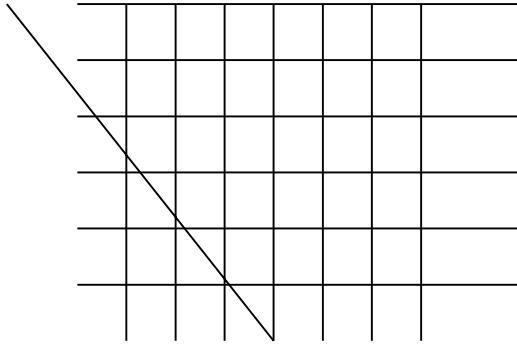


Figure 21. Blanking time of VSUVP (t_{VS-UVP}) vs. Temperature

Figure 22. VDD Over Voltage Protection Threshold (V_{DD-OVP}) vs. Temperature

FAN105BM6X

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V_{VS} regulated boundary are between $V_{VS-EAV-H}$ and $V_{VS-EAV-L}$. After exit DPGN, internal regulation reference voltage was changed to V_{VR} .

FAN105B DPGN entry and exit criteria showed as below:

DPGN entry need to meet both criteria as below:

Minimum frequency ($f_{OSC-MIN}$) operation continues over than $N_{DPGN-Entry}$ switching cycles.

$EAV > V_{VS-EAV-H}(2.550V)$.

DPGN exit criteria, meet one of below criteria:

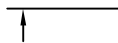
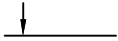
$EAV < V_{VS-EAV-L}(2.525V)$ and maximum on time at DPGN.

$EAV < V_{VS-EAV-DYN}(2.4V)$.

During the DPGN mode controlling, FAN105B decreases the operating current

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- A. THIS PACKAGE CONFORMS TO JEDEC MO-178, VARIATION AB.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- D. DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSIONS.
- E. DIMENSIONS AND TOLERANCING AS PER ASME Y14.5M-1994
- F. DRAWING FILE NAME: MA06EREV2

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